

# High Performance Microstrip Low Pass Filter for Wireless Communications

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**Abstract** A microstrip low-pass filter using T-shaped resonators is designed to achieve an ultra-sharp transition band and high suppression level. The performance of the resonators is investigated based on an LC equivalent circuit and a transfer function to compute the equations of the transmission zeros. This filter has an acceptable stopband with high insertion loss (28 dB) by adopting a rectangular suppressor. Also, the width of the transition band is 0.09 GHz (with  $-3$  and  $-40$  dB attenuation levels), that exhibits a very high sharpness ( $\xi = 411$  dB/GHz). The proposed filter with a 3 dB cut-off frequency ( $f_c$ ) of 1.32 GHz presents a high return loss in the passband (17 dB) and high figure of merit of 57,073. The designed filter is fabricated and measured, demonstrating sufficient agreement between the simulation and experimental results.

**Keywords** T-shaped resonator · LC equivalent circuit · Microstrip filter · Rectangular stub

## 1 Introduction

To reject unwanted signals, microstrip LPFs with high insertion loss in the stopband, sharp cut-off and low cost are utilized in wireless circuits [1]. In [2], a hairpin LPF with high return loss in the passband was presented; nonetheless the sharpness of the transition band is poor. In [3], a novel LPF using multi-mode resonators was reported. For increasing the stopband width, two small multi-mode stubs were utilized; however, slow cut-off

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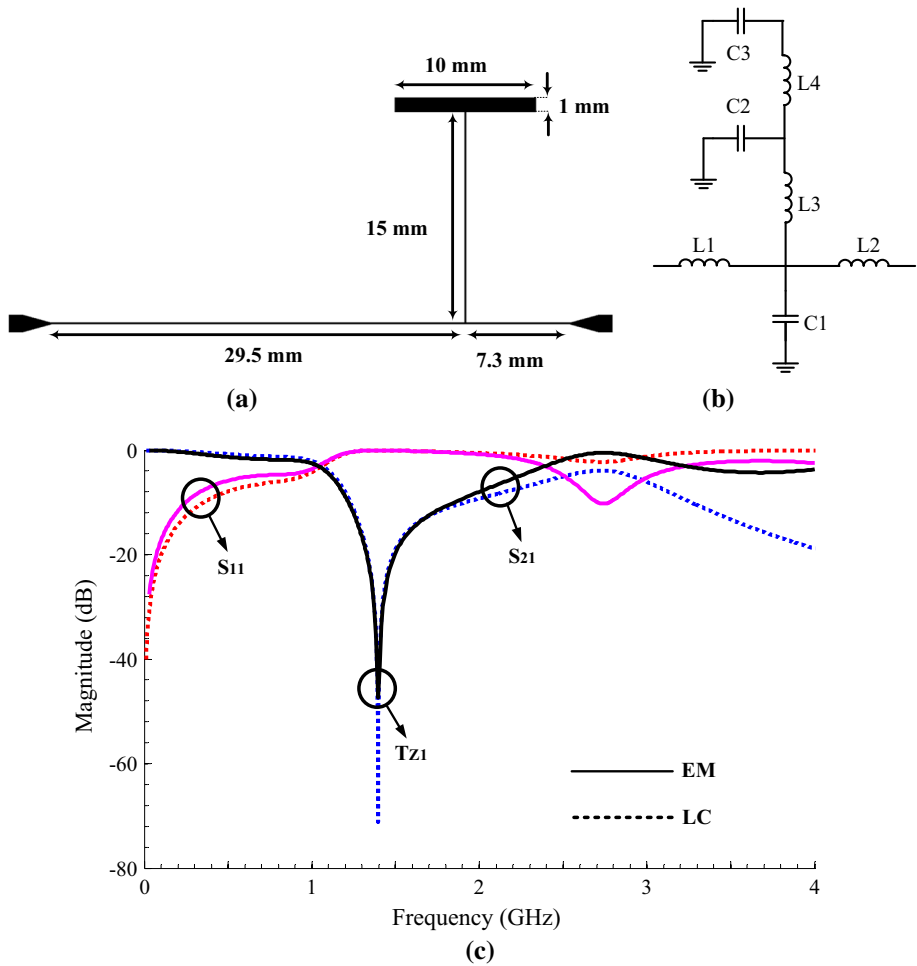
frequency, low insertion loss in the stopband and low return loss in the passband are undesired features of this work. In [4], a hairpin filter with small dimensions was studied. Slow transition band and low suppression level are drawbacks of this work. A dual-layer LPF using a stepped-impedance resonator was presented in [5]. To expand the stopband width, a defected ground plane was added; nevertheless this filter does not have a sharp cut-off and has high insertion loss in the passband. In [6], an LPF using a dual-layer structure was fabricated. In this filter, a defected ground plane was adopted to approach a sharp transition band, although it suffers from a complex structure and weak sharpness. An LPF with low suppression level, complex structure and slow transition band was reported in [7]. By adopting several stepped-impedance stubs, an LPF with a simple topology was fabricated in [8]. Weak sharpness and enormous size are disadvantages of this filter. A hairpin LPF with large size and weak sharpness in the passband was designed in [9]. To extend the stopband width, two hairpin resonators were cascaded in this filter. In [10], a microstrip LPF using dual-plane structure was reported that it have a weak harmonic suppression under  $-20$  dB suppression level and slow cut-off frequency. An LPF with high suppression level in the stopband area using an spiral transmission line and stepped-impedance stubs was introduced in [11]. In [12], an LPF with small dimensions and simple topology using stepped-impedance structures was designed that its cut-off frequency is not so sharp. A microstrip filter using dual plane structure was fabricated in [13]. High return loss and sharp transition-band are benefits of this work. A dual-layer LPF using open-circuited stubs was presented in [14], unfortunately it suffers from complex structure, large size and weak sharpness. In [15–17], dual-plane LPFs were designed that they do not have a sharp cut-off frequency and small dimensions. A symmetrical LPF using P-shaped and Lattice-Shaped resonators was introduced in [18]. Although the return loss in the passband is high, the dimensions of this filter are very large. In [19, 20], slow transition-band is the greatest problem of these LPFs. In [21], to increase the stopband width, stepped-impedance stubs are adopted at the beginning and end of transmission line; however, the sharpness of transition-band is weak. In [22], for achieving a compact size, an spiral transmission line was utilized. Also, the limited stopband and weak sharpness are problems of this circuit.

In this work, a low-pass filter with high return loss in the passband and ultra-sharp transition band is presented. This filter is composed of T-shaped resonators and one rectangular stub as a suppressing unit. Also, to achieve a compact size, this structure is bent.

## 2 Design Process

### 2.1 T-Shaped Resonator

Figure 1a exhibits a T-shaped resonator composed of a high impedance stub and one rectangular open-circuited stub, which they are connected to the transmission line. The LC equivalent circuit of this resonator is presented in Fig. 1b. The transmission line with  $L_1$ ,  $L_2$  and  $C_1$  is modelled as inductances and capacitance, respectively.  $L_3$  and  $C_2$  exhibit the inductance and capacitance of the high-impedance stub and  $L_4$  and  $C_3$  are equivalent inductance and capacitance of the open-circuited stub. The values of the lumped elements using equations cited in [1] are computed and they are as follows:  $L_1 = 16.34$  nH,  $L_2 = 5.21$  nH,  $L_3 = 10.22$  nH,  $L_4 = 1.164$  nH,  $C_1 = 1.11$  pF,  $C_2 = 0.22$  pF and  $C_3 = 0.96$  pF. The EM and LC simulation results of the T-shaped resonator are depicted in



**Fig. 1** T-shaped resonator: **a** layout, **b** LC equivalent circuit, **c** EM and LC simulations

Fig. 1c. As seen, this structure has a sharp transition band and produces a transmission zero (TZ<sub>1</sub>) at 1.4 GHz, that transition band is tuned by it. To obtain the equation of the TZ<sub>1</sub>, the transfer function is presented in Eq. (1), that  $r$  is the matching impedance of input and output ports ( $r = 50 \Omega$ ). Here, TZ<sub>1</sub> is calculated by equalling numerator of transfer function with zero in Eq. (2).

$$\frac{V_o}{V_i} = \frac{2r}{L_2 S (L_1 C_1 S^2 + b + 1) + r (L_1 C_1 S^2 + a L_2 S + b + 2) + r^2 a + L_1 S}, \quad (1)$$

where

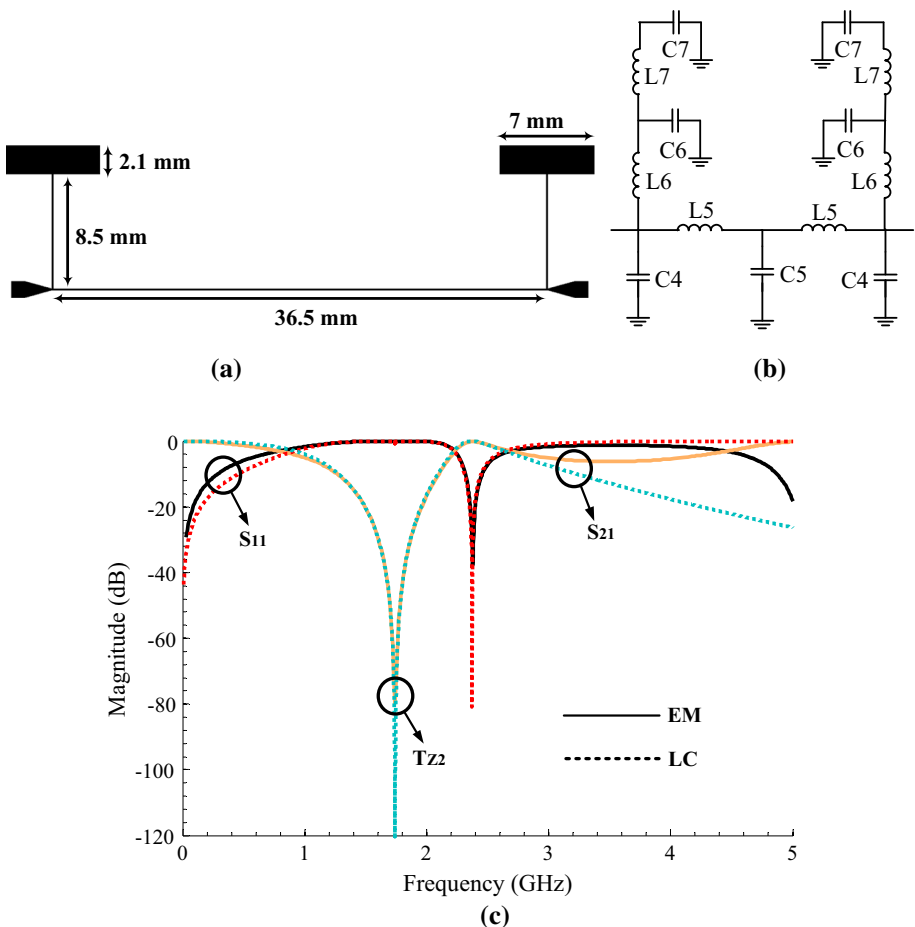
$$a = \frac{C_2 C_3 L_4 S^3 + (C_2 + C_3) S}{C_2 C_3 L_4 L_3 S^4 + (C_2 L_3 + C_3 L_3 + C_3 L_4) S^2 + 1} + C_1 S,$$

$$b = \frac{L_1 S (C_2 C_3 L_4 S^3 + (C_2 + C_3) S)}{C_2 C_3 L_4 L_3 S^4 + (C_2 L_3 + C_3 L_3 + C_3 L_4) S^2 + 1}.$$

$$T_{Z1} = \frac{1}{2\pi \sqrt{(C_2 C_3 L_4 L_3) + (C_2 L_3 + C_3 L_3 + C_3 L_4)}}. \quad (2)$$

## 2.2 Dual T-Shaped Resonator

The layout of the dual T-shaped resonator is illustrated in Fig. 2a. This resonator with shunt capacitors and series inductors is modelled in Fig. 2b. The values of the LC equivalent circuit are as follows:  $L_5 = 10.78$  nH,  $L_6 = 6.036$  nH,  $L_7 = 0.156$  nH,  $C_4 = 0.5$  pF,  $C_5 = 0.71$  pF,  $C_6 = 0.4$  pF and  $C_7 = 0.966$  pF. The EM and LC simulation results are depicted in Fig. 2c. This structure can improve the suppression level by producing a transmission zero (TZ<sub>2</sub>) at 1.78 GHz. The transfer function of the dual T-shaped



**Fig. 2** Dual T-shaped resonator: **a** layout, **b** LC equivalent circuit, **c** EM and LC simulations

resonator is displayed in Eq. (3). Also, the equation of the TZ<sub>2</sub> is obtained from Eq. (3) and shown in Eq. (4).

$$\frac{V_o}{V_{in}} = \frac{2Z_0d}{dL_5S + dL_5S(C_5L_5S^2 + 1) + Z_0^2c + Z_0^2(a + b + 1)c + dZ_0^2C_5S(b + 1) + Z_0da + Z_0dC_5L_5S^2 + Z_0(L_5S + L_5S(C_5L_5S^2 + 1))c + Z_0db + 2Z_0d}, \quad (3)$$

where

$$a = L_5S\left(\frac{c}{d} + C_5S(b + 1)\right),$$

$$b = \frac{cL_5S}{d},$$

$$c = C_4C_6C_7L_7L_6S^5 + (C_4C_6L_6 + C_4C_7L_6 + C_4C_7L_7 + C_6C_7L_7)S^3 + (C_4 + C_6 + C_7)S,$$

$$d = (C_6C_7L_7L_6S^4 + (C_6L_6 + C_7L_6 + C_7L_7)S^2 + 1).$$

$$T_{Z2} = \frac{1}{2\pi\sqrt{(C_6C_7L_6L_7) + (C_6L_6 + C_7L_6 + C_7L_7)}}. \quad (4)$$

### 2.3 Rectangular Resonator

The layout and LC equivalent circuit of rectangular resonator are displayed in Fig. 3a, b. In this model, L<sub>8</sub>, L<sub>9</sub> and C<sub>8</sub> are inductances and capacitance of transmission line. Also, L<sub>10</sub> and C<sub>9</sub> denote inductance and capacitance of rectangular stub. The values of these parameters are as follows: L<sub>8</sub> = 9.6 nH, L<sub>9</sub> = 12 nH, L<sub>10</sub> = 2.41 nH, C<sub>8</sub> = 3.7 pF and C<sub>9</sub> = 0.49 pF. Figure 3c shows EM and LC simulation results of this structure. As seen, this circuit generates a transmission zero (TZ<sub>3</sub>) at 4.6 GHz that to compute the equation of TZ<sub>3</sub>, the transfer function of rectangular stub is achieved from its LC equivalent circuit. The transfer function and equation of TZ<sub>3</sub> are presented in Eqs. (5) and (6), respectively.

$$\frac{V_o}{V_{in}} = \frac{2Z_0(C_9L_{10}S^2 + 1)}{L_8S(C_9L_{10}S^2 + 1) + aL_9L_8S^2 + L_9S(C_9L_{10}S^2 + 1) + aZ_0^2 + (aZ_0L_8 + aZ_0L_9)S + 2Z_0(C_9L_{10}S^2 + 1)}, \quad (5)$$

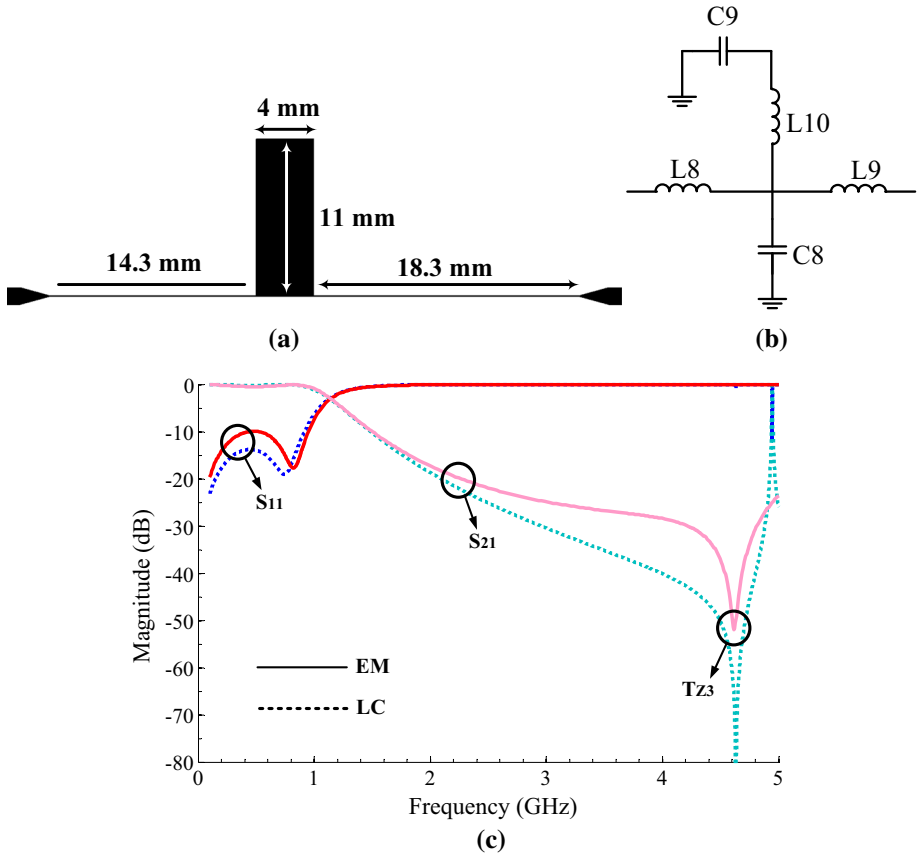
where

$$a = C_8S + C_9S + C_9C_8L_{10}S^3.$$

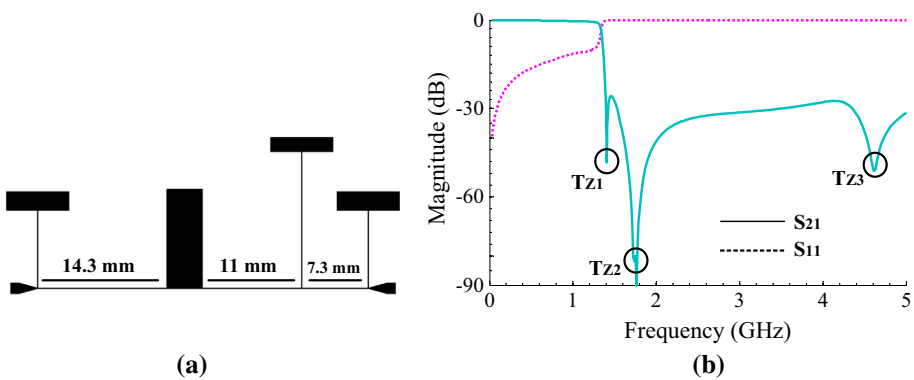
$$T_{Z3} = \frac{1}{2\pi\sqrt{C_9L_{10}}}. \quad (6)$$

### 2.4 LPF Design

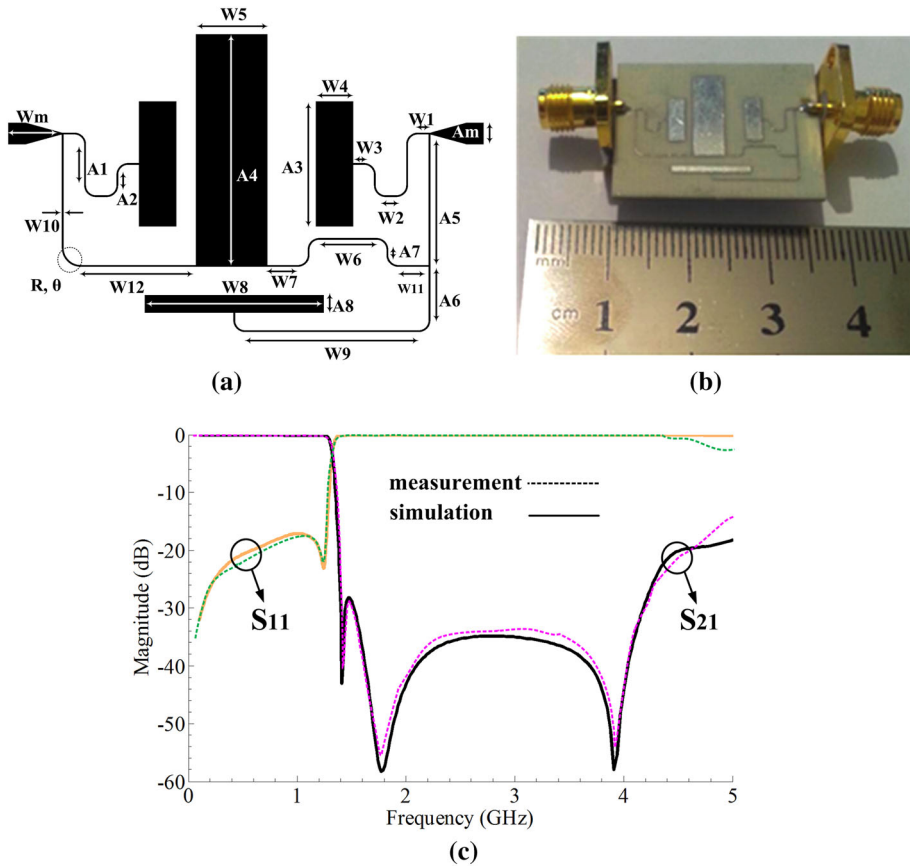
To design a high performance low-pass filter, T-shaped resonators and rectangular stub (as suppressing unit) are combined, as depicted in Fig. 4a. The primitive LPF has an acceptable stopband with high insertion loss and sharp cut-off frequency (seen in Fig. 4b), but the circuit dimensions are large. However, we have achieved a compact layout, as seen



**Fig. 3** Rectangular resonator: **a** layout, **b** LC equivalent circuit, **c** EM and LC simulations



**Fig. 4** Primitive LPF: **a** layout, **b** EM simulation



**Fig. 5** Proposed LPF: **a** layout, **b** fabricated photo, **c** simulation and measurement results

in Fig. 5a. The proposed filter shows 44% size reduction in comparison with previous structure.

### 3 Simulated and Measured Results

The proposed filter with 3 dB cut-off frequency of 1.32 GHz is fabricated on a substrate (Rogers\_RO4003) with  $\epsilon_r = 3.38$ , thickness = 0.508 mm and loss-tangent = 0.002 (As illustrated in Fig. 5b) and tested using an Agilent N5230A network analyser. The simulation results are taken by the ADS software. The simulation and measurement results are depicted in Fig. 5c.

The final LPF with high return loss (RL) in the passband (17 dB) has an ultra-sharp transition band ( $\xi = 411$  dB/GHz) from 1.32 to 1.41 GHz (with  $-3$  and  $-40$  dB attenuation levels). The stopband with excellent suppression level ( $-28$  dB) is extended from 1.4 to 4.218 GHz ( $3.19 f_c$ ).

The circuit dimensions are  $0.158\lambda_g \times 0.128\lambda_g$ , where  $\lambda_g$  is guided wave-length at  $f_c$ . Finally, the designed LPF presents a high FOM of 57,073. The physical dimensions of this

**Table 1** Comparison among reported works and proposed one

| References | $\xi$ | SF  | RSB   | NCS                  | AF | FOM    | RL   |
|------------|-------|-----|-------|----------------------|----|--------|------|
| [2]        | 52.8  | 2   | 1.529 | $0.081 \times 0.113$ | 1  | 17,640 | 23   |
| [3]        | 16.5  | 1.5 | 1.58  | $0.090 \times 0.110$ | 1  | 3950   | 10   |
| [4]        | 95    | 2   | 1.4   | $0.104 \times 0.214$ | 1  | 7388   | 16   |
| [5]        | 188   | 2   | 0.9   | $0.200 \times 0.180$ | 2  | 4700   | 10   |
| [6]        | 162   | 2.5 | 1.124 | –                    | 2  | –      | 15   |
| [7]        | 256   | 1.5 | 1.574 | $0.148 \times 0.157$ | 1  | 38747  | 10   |
| [13]       | 159   | 2   | 1.146 | $0.316 \times 0.689$ | 2  | 837    | 12.5 |
| [17]       | 29.3  | 2.4 | 1.534 | 0.0075               | 2  | 7191.4 | 20   |
| [18]       | 100   | 2   | 1.58  | $0.184 \times 0.478$ | 1  | 3593   | 19   |
| [21]       | 94    | 2.3 | 1.262 | $0.244 \times 0.169$ | 1  | 6616.7 | 17   |
| [22]       | –     | 2   | 0.332 | $0.337 \times 0.253$ | 1  | –      | 20   |
| This work  | 411   | 2.8 | 1.003 | $0.158 \times 0.128$ | 1  | 57,073 | 17   |

filter are as follows:  $A_1 = 2.3$ ,  $A_2 = 0.6$ ,  $A_3 = 7$ ,  $A_4 = 13$ ,  $A_5 = 7.3$ ,  $A_6 = 3$ ,  $A_7 = 0.31$ ,  $A_8 = 1$ ,  $A_m = 1.2$ ,  $W_1 = 0.6$ ,  $W_2 = 0.6$ ,  $W_3 = 0.6$ ,  $W_4 = 2.1$ ,  $W_5 = 4$ ,  $W_6 = 3.2$ ,  $W_7 = 1.7$ ,  $W_8 = 10$ ,  $W_9 = 9.7$ ,  $W_{10} = 0.1$ ,  $W_{11} = 1.7$ ,  $W_{12} = 6.43$ ,  $W_m = 3$ ,  $R = 1$  (all in millimeters) and  $\theta = 90^\circ$ . The proposed filter and reported works are compared in Table 1 based on parameters outlined in [23, 24].

As shown in Table 1, our filter has the sharpest cut-off frequency, the highest suppression level and the highest FOM in comparison with published works in [2–6]. Transition band sharpness ( $\xi$ ) is for  $-3$  and  $-40$  dB suppression points. The table also lists the suppression factor (SF) and RSB is the relative stopband band-width. The normalized circuit size is given by NCS. AF is architecture factor and FOM is figure of merit [ $FOM = (\xi \times RSB \times SF)/(NCS \times AF)$ ].

## 4 Conclusion

A microstrip low-pass filter using T-shaped resonators (to approach sharp cut-off and high suppression level) and one rectangular stub (to increase the stopband width) has been designed, fabricated and tested. This filter presents excellent features like, simple topology, narrow transition band (0.09 GHz), high insertion loss in the stopband (28 dB), small dimensions and very high FOM of 57,073. The final structure with 3 dB cut-off frequency of 1.32 GHz is suitable for wireless communications.

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